

國立高雄海洋科技大學 100 學年度碩士班考試入學  
微電子工程研究所—微電子學試題  
(※須使用計算機)

1. Derive the closed-loop input resistance at the noninverting terminal of a noninverting amplifier, as shown in Fig.1. (20%)

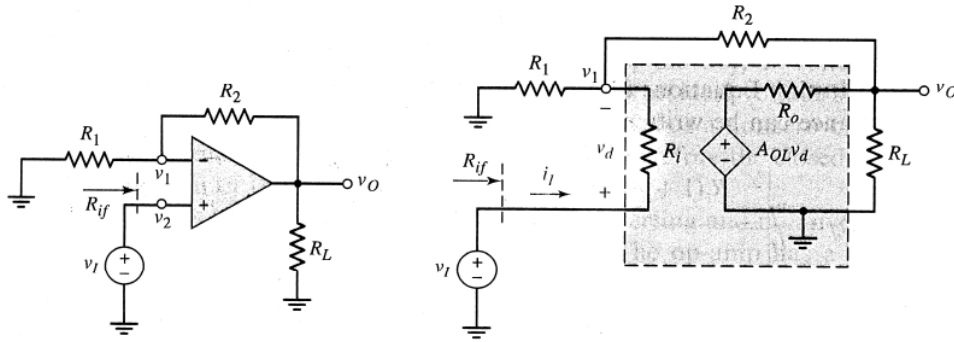


Fig.1

2. Determine the bias current effect in an op-amp circuit, (a) without bias current compensation, as shown in Fig. 2, and (b) with bias current compensation, as shown in Fig. 3. ( $R_1=10\text{ k}\Omega$ ,  $R_2=100\text{ k}\Omega$ ,  $I_{B1}=1.1\text{ }\mu\text{A}$ ,  $I_{B2}=1.0\text{ }\mu\text{A}$ )(hint:  $R_3= R_1//R_2$ ) (10%)

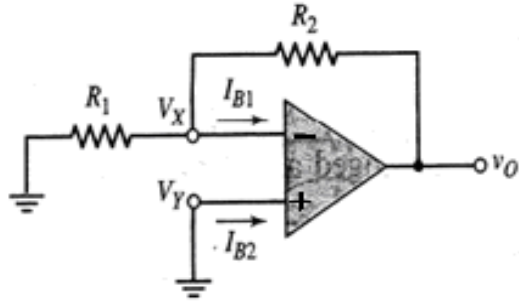


Fig.2

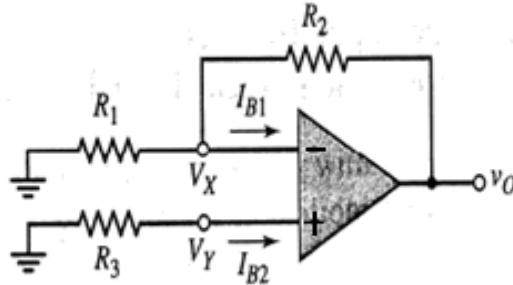


Fig.3

3. The Common-emitter circuit in Fig. 4 is biased at  $V_{cc}=20\text{V}$ . The maximum transistor power is  $P_{D,max}=20\text{W}$  and the current gain is  $\beta=80$ . (a) Determine  $R_L$  and  $R_B$  such that the maximum power is delivered to the load  $R_L$ . (b) find the value of  $V_p$  for the input signal that delivers the maximum power. (15%)
4. Figure 5 shows a basic two-transistor pnp current source. The transistor parameters are  $V_{EB(on)}=0.7\text{V}$ ,  $\beta=40$ , and  $V_A=\infty$ . Design the circuit such that  $I_o=0.25\text{mA}$  and determine the value of  $I_{REF}$ . (15%)

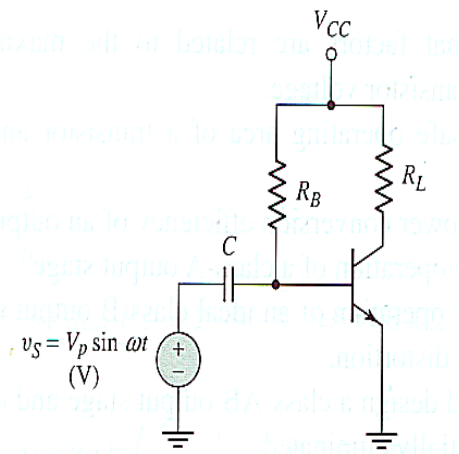


Fig. 4

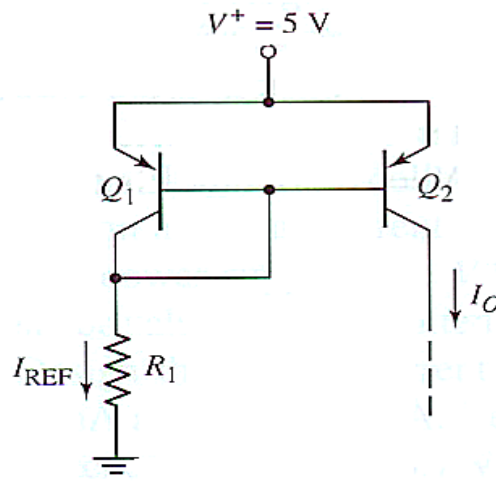


Fig. 5

5. 試解釋以下觀念:

(a)請敘述 P 型半導體與 N 型半導體結合成 PN 二極體所形成內建電位的過程?為何內建電位存在是必須的?

(b)可否利用三用電錶(最小可測到 0.03V)來測試 PN 二極體的內建電位?並解釋之。

(c) PN 二極體從順偏切換到逆偏(如圖 6 所示)則電流是否立即關閉?原因為何? (20%)

6. The ac equivalent circuit of a CMOS common-gate circuit is shown in Fig. 7. The transistor parameters for M1 are :  $V_{TN} = 0.5V$ ,  $k_n = 85 \mu A/V^2$ ,  $(W/L)_1 = 50$ ,  $\lambda_1 = 0.05 V^{-1}$ , and for M2 and M3 are  $V_{TP} = -0.5V$ ,  $k_p = 40 \mu A/V^2$ ,  $(W/L)_{2,3} = 50$ ,  $\lambda_{2,3} = 0.075 V^{-1}$ . Determine the (a) small-signal parameter of the circuit (b) small-signal voltage gain and (c) input resistance  $R_i$  (d) output resistance  $R_o$ . (20%)

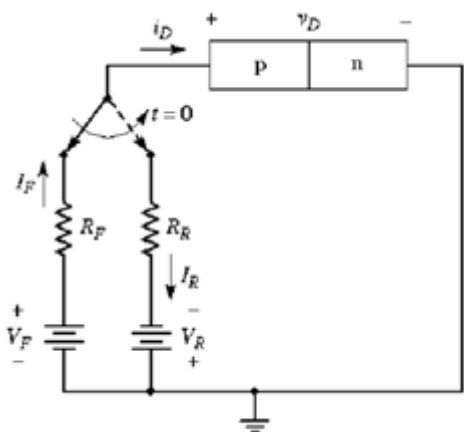


Fig. 6

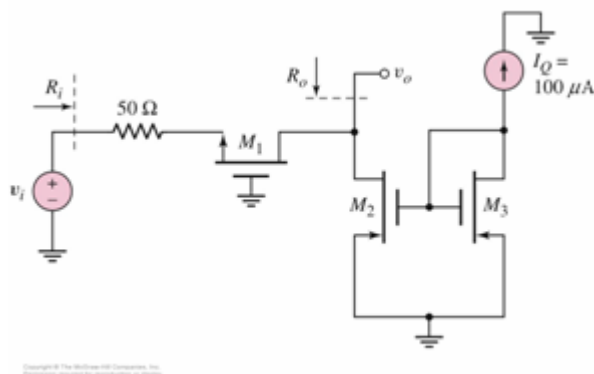


Fig. 7

「試題結束」